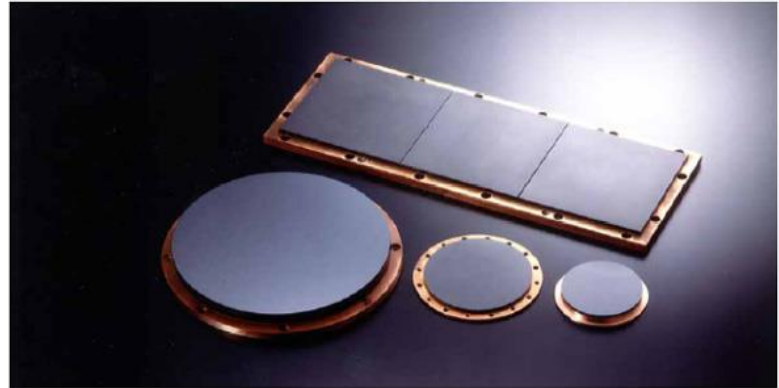


Advansic High Purity SiC Sputtering Target

Features

- Enable to achieve high deposition rate by DC sputtering.
(Over twice as fast than RF sputtering)
- Easy to produce uniform and high dense films.
- Fewer particles and dusts
- Enable to apply high electric power.



Properties

Grade	SSC				CSI
	S312	S314	S511	S452	S202
Code	β -SiC	β -SiC	β -SiC*	α -SiC	β -SiC,C
Crystalline	β -SiC	β -SiC	β -SiC*	α -SiC	β -SiC,C
Bulk Density (kg/m ³ × 10 ³)	3.19	3.18	3.18	3.20	2.50
Four-point bending strength Mpa at room temperature	520	650	470	490	160
Vickers hardness	2700	2270	2250	2700	—
Young's modulus	420	420	410	430	—
Coefficient of Thermal expansion × 10 ⁻⁶ (1073K)	4.0	4.9	4.9	4.8	—
Thermal conductivity w/m-K at room temperature (W/m·K)	194	190	190	247	60
Electric resistivity at room temperature ($\Omega \cdot m \times 10^{-2}$)	0.01	0.006	0.03	130	0.005

* Include α -SiC

Material Grades and Deposition Applications

SSC Grade (for SiC film) Excellent abrasion resistance, anti- erosion, high refractive index and high adhesion coating

CSI Grade (for SiC and Carbon film) Excellent abrasion resistance, low friction and high adhesion coating

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